

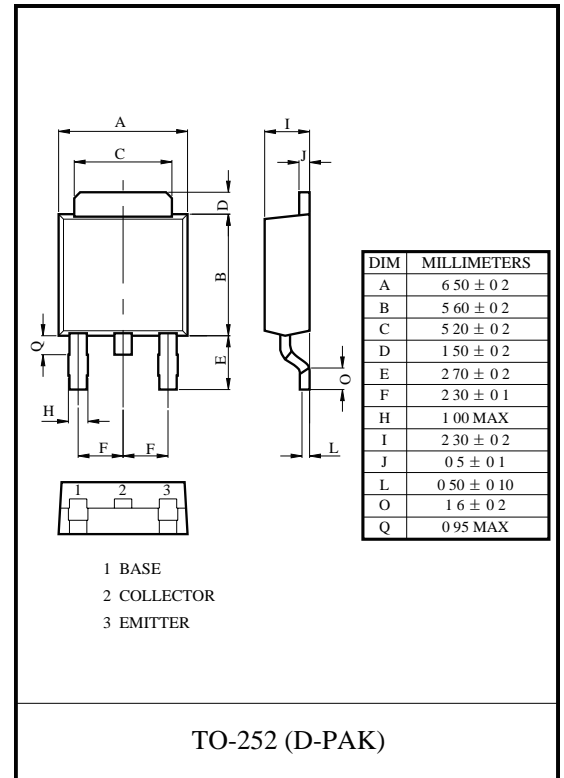
FTA1952 TRANSISTOR (PNP)

FEATURES

- - 5A, - 60V Middle Power Transistor
- Suitable for Middle Power Driver
- Complementary NPN Types : FTC5103
- Low Collector- emitter saturation voltage

APPLICATIONS

- Middle Power Driver
- LED Driver
- Power Supply



MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Collector- Base Voltage	V_{CB0}	- 100	V
Collector- Emitter Voltage	V_{CEO}	- 60	V
Emitter- Base Voltage	V_{EBO}	- 5	V
Collector Current	I_C	- 5	A
Collector Power Dissipation	$P_C^{(1)}$	1	W
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	125	°C/W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	- 55~ +150	°C

(1). Mounted on a substrate



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector - base breakdown voltage	V _{(BR)CBO}	I _C = - 50μA, I _E =0	- 100			V
Collector - emitter breakdown voltage	V _{(BR)CEO}	I _C = - 1 mA, I _B =0	- 60			V
Emitter - base breakdown voltage	V _{(BR)EBO}	I _E = - 50μA, I _C =0	- 5			V
Collector cut - off current	I _{CBO}	V _{CB} = - 100V, I _E =0			- 10	μA
Emitter cut - off current	I _{EBO}	V _{EB} = - 5V, I _C =0			- 10	μA
DC current gain	h _{FE(1)} *	V _{CE} = - 2V, I _C = - 1A	120		270	
	h _{FE(2)} *	V _{CE} = - 2V, I _C = - 3A	40			
Collector - emitter saturation voltage	V _{CE(sat)} *	I _C = - 3A, I _B = - 0.15A			- 0.3	V
		I _C = - 4A, I _B = - 0.2A			- 0.5	V
Base - emitter saturation voltage	V _{BE(sat)} *	I _C = - 3A, I _B = - 0.15A			- 1.2	V
		I _C = - 4A, I _B = - 0.2A			- 1.5	V
Collector output capacitance	C _{ob}	V _{CB} = - 10V, I _E =0, f=1MHz		130		pF
Transition frequency	f _T *	V _{CE} = - 10V, I _C = - 0.5A, f=30MHz		80		MHz
Turn - on time	t _{on}	V _{CC} = - 30V, I _C = - 3A, I _{B1} = - I _{B2} =150mA			0.3	μs
Storage time	t _s				1.5	μs
Fall time	t _f				0.3	μs

Notes:

1. Pulse Test : Pulse Width ≤ 300μs, duty cycle ≤ 2%.

Typical Characteristics

